ROCHESTER INSTITUTE OF TECHNOLOGY MICROELECTRONIC ENGINEERING

MEMS Accelerometer Laboratory

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3-26-2014 Accelerometer_lab.ppt

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OUTLINE

Introduction **Cantilever Based Accelerometers** Analog Devices Inc., Accelerometers Analog Output Pulse Width Output Fabrication of RIT Accelerometers **RIT** Accelerometers **Test Fixture Example Calculations** Measured Results for ADXL203 Measured Results for RIT Devices Laboratory Assignment References

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INTRODUCTION

Acceleration (a) is the term given to the condition where and object experiences a change in velocity (v). Objects of mass (m) experience a force (F) equal to m times a. (F = ma)Earths gravity exerts an acceleration on objects creating a force. The acceleration due to gravity (g) has been found to be 9.8m/s^2 . Acceleration, velocity and position (x) of objects are related by the following equation:

$$a = dv/dt = d^2x/dt^2$$

Rochester Institute of Technology Microelectronic Engineering Acceleration

Earths Gravity	1g
Standing on the moon	0.16g
Passenger Car in a Turn	2g
Indy Car in a Turn	3 g
Bobsled in a Turn	5g
Human	7g
Unconsciousness	
Human Death	50g
Car Crash Survival	100g
Mechanical Watch	5,000g
Electronics in Artillery	15,000g
Haldron Collider	1.9E8g

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INTRODUCTION

An accelerometer is a sensor that can be used to measure acceleration. These sensors are used in systems for car air bag deployment, tilt sensing, and motion control. Most accelerometers are sensors that measure the force on a known mass (proof mass). The proof mass is supported by a spring, of spring constant (k), that will create a force equal and opposite to the force due to acceleration. The position is measured in response to changes in acceleration. There is also a friction or damping force.



INTRODUCTION

One type of accelerometer is based on a cantilever beam (spring) with a mass (m) at the free end and integrated resistors (R) positioned to measure strain as the cantilever bends in response to acceleration.



EQUATIONS FOR CANTILEVER BEAM

The maximum deflection is at the free end of the cantilever $Ymax = F L^{3/3EI}$

where E = Youngs Modulus and $I = bh^3/12$, moment of inertia

The maximum stress $(\sigma_{x=0})$ is at the top surface of the cantilever beam at the anchor where x=0

 $\sigma_{x=0} = F Lh/2I$

The resonant frequency (f_0) of the cantilever beam is

 $f_0 = 1/2\pi \{3EI / (L^3(m+0.236m_B))\}^{0.5}$

where m_B is the beam mass and m is end mass and E is Young's Modulus for beam material

> <u>Mechanics of Materials</u>, by Ferdinand P. Beer, E. Russell Johnston, Jr., McGraw-Hill Book Co.1981

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FINITE ELEMENT ANALYSIS (FEA) OF CANTILEVER



SolidWorks

Length = $1500 \ \mu m$ Width = $600 \ \mu m$ Thickness = $20 \ \mu m$ Window ~ $300 \ x \ 300 \ \mu m$



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RIT ACCELEROMETERS



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ADI ACCELEROMETERS



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ANALOG DEVICES INC. (ADI) ACCELEROMETERS

15 years ago, Analog Devices revolutionized automotive airbag systems with its unique *i*MEMS® (integrated Micro Electro Mechanical System) technology. *i*MEMS accelerometers were the first products in an array of MEMS inertial sensor solutions to use innovative design techniques to integrate small, robust sensors with advanced signal conditioning circuitry on a single chip. Today, ADI offers the industry's broadest accelerometer portfolio, with products addressing a range of user needs including high performance, low power consumption, integrated functionality, and small size.





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ADXL203 Dual Axis Analog Output

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ANALOG DEVICES INC. (ADI) ACCELEROMETERS

ADXL278



Evaluation Board



http://www.analog.com



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ADXL203 ANALOG OUTPUT ACCELEROMETER

The ADXL103/ADXL203 are high precision, low power, complete single- and dual-axis accelerometers with signal conditioned voltage outputs, all on a single, monolithic IC. The ADXL103/ADXL203 measure...<u>More</u>

New! Tighter specifications on sensitivity, cross-axis sensitivity, and non-linearity.





ADXL330 THREE AXIS ANALOG OUTPUT





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Close this Window

ADXL330 Small, Low Power, 3-Axis ±3g iMEMS® Accelerometer

Product Description

The ADXL330 is a small, thin, low power, complete 3-axis accelerometer with signal conditioned voltage outputs, all on a single monolithic IC. The product measures acceleration with a minimum full-scale range of ±3 g. It can measure the static acceleration of gravity in tilt-sensing applications, as well as dynamic acceleration resulting from motion, shock, or vibration.

The user selects the bandwidth of the accelerometer using the C_X , C_Y , and C_Z capacitors at the X_{OUT} , Y_{OUT} , and Z_{OUT} pins. Bandwidths can be selected to suit the application, with a range of 0.5 Hz to 1600 Hz for X and Y axes, and a range of 0.5 Hz to 550 Hz for the Z axis.

The ADXL330 is available in a small, low profile, 4 mm × 4 mm × 1.45 mm, 16-lead, plastic lead frame chip scale package (LFCSP_LQ).

Price ~ \$5.50 ea



Applications:

Cost-sensitive, low-power, motion- and tilt-sensing applications Mobile devices Gaming system Disk drive protection

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ADXL213 PULSE WIDTH OUTPUT ACCELEROMETER



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04742-0-016

TILT SENSING WITH ADXL213



PULSE WIDTH ACCELEROMETER MOVIE





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MASKS





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TOP HOLE BULK MEMS PROCESS FLOW

- 1. Obtain qty 10, 4" n-type wafers
- 2. CMP back side
- 3. CMP Clean
- 4. RCA Clean
- 5. Grow masking oxide 5000 Å, Recipe 350
- 6. Photo 1: P++ diffusion
- 7. Etch Oxide, 12 min. Rinse, SRD
- 8. Strip Resist
- 9. Spin-on Glass, Borofilm 100, include dummy
- 10. Dopant Diffusion Recipe 110
- 11. Etch SOG and Masking Oxide, 20min BOE
- 12. Four Point Probe Dummy Wafer
- 13. RCA Clean
- 14. Grow 500 Å pad oxide, Recipe 250
- 15. Deposit 1500 Å Nitride
- 16. Photo 2: for backside diaphragm
- 17. Spin coat Resist on front side of wafer
- 18. Etch oxynitride, 1 min. dip in BOE, Rinse, SRD 39. Photo 4, Contact Cut
- 19. Plasma Etch Nitride on back of wafer, Lam-490 40. Etch in BOE, Rinse, SRD
- 20. Wet etch of pad oxide, Rinse, SRD
- 21. Strip Resist both sides



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- 22. Etch Diaphragm in KOH, ~8 hours
- 23. Decontamination Clean
- 24. RCA Clean
- 25. Hot Phosphoric Acid Etch of Nitride
- 26. BOE etch of pad oxide
- 27. Grow 5000Å oxide
- 28. Deposit 6000 Å poly LPCVD
- 29. Spin on Glass, N-250
- 30. Poly Diffusion, Recipe 120
- 31. Etch SOG
- 32.4 pt Probe
- 33. Photo 3, Poly
- 34. Etch poly, LAM490
- 35. Strip resist
- 36. RCA Clean
- 37. Oxidize Poly Recipe 250
- 38. Deposit 1µm LTO

- - 41. Strip Resist
 - 42. RCA Clean, include extra HF
- 43. Deposit Aluminum, 10,000Å 44. Photo 5, Metal 45. Etch Aluminum, Wet Etch 46. Strip Resist 47. Deposit 1µm LTO 48. Photo 6, Via 49. Etch Oxide in BOE, Rinse, SR 50. Strip Resist 51. Deposit Aluminum, 10,000Å 52. Photo 7. Metal 53. Etch Aluminum, Wet Etch 54. Strip Resist 55. Deposit 1µm LTO 56. Deposit Aluminum, 10,000Å 57. Photo 8, Top Hole 58. Top hole aluminum etch 59. Diaphragm thinning option 60. Top hole Silicon etch
- 61. Test

62. Package and add solder ball

3-15-07

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TEST FIXTURE MOVIE

Accelerometer Test Fixture

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STRAIN GAGE – POSITION SENSOR



A strain gage is used to measure position. It is a foil resistor glued on the cantilever beam near the anchor. If the tip of the cantilever is moved up or down the strain well cause a small change in the resistance of the gage and a change in Vout.



VELOCITY SENSOR

A coil in a changing magnetic field will generate a voltage.

Faraday's Law of Electromagnetic Induction

 $EMF = -\Delta \Phi/\Delta t = -N Area \Delta \Phi/\Delta t$



http://micro.magnet.fsu.edu/electromag/java/faraday2/

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EDDY CURRENT DAMPER

The copper pipe is a coil (one turn) and if placed in a moving magnetic field will generate a voltage and since the coil is a closed loop there will be an electrical current (eddy current). The current moving in a loop will create a magnetic field and the field will oppose the magnetic field that created it. The opposing force dampens the oscillations of the vibrating beam.



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PICTURES OF RIT ACCELEROMETERS

RIT made Accelerometers Pictures





5mm x 5mm chip

Rochester Institute of Technology Microelectronic Engineering One accelerometer with solde ball proof mass.

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PACKAGED RIT ACCELEROMETERS



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THE TEST FIXTURE



EXAMPLE CALCULATIONS FOR TEST FIXTURE

The resonant frequency (f_0) of the test fixture

 $f_0 = 1/2\pi \ \{3EI \ / \ (L^3(m+0.236m_B))\}^{0.5}$

where m_B is the beam mass and m is end mass and E is Young's Modulus for the beam material $I = b h^3 / 12$, moment of inertia

Then we write an expression for the position of the end of the beam on the test fixture after deflecting the beam by Ao and releasing.

 $X(t) = -Ao \cos (2 \pi f_0 t)$

Taking the second derivative we write an expression for the acceleration experienced at the end of the beam on the test fixture.

$$a = d^2 X(t)/dt^2 = Ao (2 \pi f_0)^2 \cos (2 \pi f_0 t)$$



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EXAMPLE CALCULATIONS FOR RIT ACCELEROMETER

The RIT accelerometer will experience a force at the end of the sensor cantilever beam equal to mass times acceleration.

 $F = ma = 4/3 \pi r^3 d Ao (2 \pi f_0)^2 \cos (2 \pi f_0 t)$

Using the maximum force we calculate the maximum stress

 $\sigma_{x=0} = F Lh/2I$

Next we calculate the maximum strain using Hooke's Law.

 $\epsilon = \sigma_{x=0} / E$ where E is Young's modulus for silicon

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EXAMPLE CALCULATIONS FOR RIT ACCELEROMETER

The nominal resistance value is found to be:

 $R = rhos L/W = 60 ohms 1000 \mu m/50 \mu mm = 1200 ohms$

The resistance value at maximum strain, R', is approximately:

R' = rhos L(1+ ε)/W

The accelerometer circuit output voltage is :

Vout = [12 R'/(R+R')] -6

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SPREAD SHEET FOR ACCELEROMETER CALCULATIONS

6/13/07

accelerometer.xls

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MICROELECTROMECHANICAL SYSTEMS Dr. Lynn Fuller, Burak Baylav

To use this spreadsheet change the values in the white boxes. The rest of the sheet is protected and should not be changed unless you are sure of the consequences. The calculated results are shown in the purple boxes.

Calculations for Cantilever Beam (Test Fisture)

Frequency of Oscillation:

Ca

	The resonant frequency	, f0 of the cantilever beam	13.48	hz
		Beam Length, L	0.4	m
$fD = 1/2\pi \{3EI / (L^3)(m+$	0.236mB))}0.5	Beam Width, b	0.025	m
	,,,,	Beam thickness, h	0.003	m
$I = b h^3$		End Mass, mB	0	Kg
	Density fo	r Material Selected Below	2.33	gm/cm3
	Beam M	ass = density x volume, m	69.9	gm
	Young's Modulus fo	r Material Selected Below	1.90E+11	N/m2
Acceleration versus time	e:			
		Initial Deflection	2	cm
$a = d2X(t)/dt2 = Ao (2 \pi)$	$(10)^{2} \cos(2\pi t 0 t)$	Maximum Acceleration	143.34	młs2
	Ma:	imum Acceleration, in g's	14.63	g's
Iculations for RIT Acceleromet	er			
Force:				
	Maximum force due t	o proof mass, Fmax = ma	8.35E-05	N
	end mass on F	IT accelerometer, m = d V	5.82E-04	gm
		volume, V = $4/3\pi r^3$	6.54E-05	cm^3
F = Fmax cos(2"p"f0"t)		radius, r =	250	μm
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SPREAD SHEET FOR ACCELEROMETER CALCULATIONS

	Accelerometer, cantilever beam bending Ymax:			7.03E-01	μm		
				L =	2000	μm	
	Ymax = F L^3/3El			b =	200	μm	
		$I = h h^{A2}$		h =	10	μm	
		1-011.5		Young's Modulus, E =	1.90E+11	N/m2	
	σ max = F L I	h721		Max Stress,σ max:			
				2.64E-08	րայիա		
	Resistor (Calculations		5400	ohms		
		Measured	Measured Sheet Resistance, Rhos = 60 ohm:				
R = Rhos L/W			Resistor Length, L =900 μr				
				Resistor Width, W =	10	μm	
R' = R + Rhos (L+ L's)/W		Resista	Resistance under Max Stress, R' = 540				
			Tdd=107	Delta R = R' - R =	0.000142375	ohms	
			Resternal	Vdd = Vss =	10	volts	
			Vox	Rexternal =	5400	ohms	
				Nominal Vout =	0	volts	
			Ø	Yout Max =	1.31829E-07	volts	
Constants:		Raccelerometer					
			V10=.10V	Select Material Using 1 or 0			
	Youngs M	lodulus(N/m2)	Density (gm/cm3)	Fizture RI	l Acceromete	ſ	
	Silicon	1.9E+11	2.33		1		
	Silicondiozide	7.30E+10	2.19	0	0		
$\overline{7}$	Silicon Nitride	3.85E+11	3.44		0		
	Aluminum	6.80E+10	3.9		0		
	Steel	2.00E+11	7.8		0		
	Brass	1.10E+11	8.55		0		
	Lead		11.34			_	
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CALCULATED PLOT OF VOUT VS. TIME



20 G ACCELEROMETER TEST SET UP



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TESTING OF PRISM PROJECT ACCELEROMETERS



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RIT 100X DIFFERENTIAL VOLTAGE AMPLIFIER







INSTURMENTATION AMPLIFIER



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CONFIRMATION OF TEST FIXTURE RESONANT FREQUENCY

+5 Volts



-5 Volts

Vout near Zero so that it can be amplified

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Strain gage output signal

Period ~ 70msec Thus frequency ~14.3 Hz

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ADI ACCELEROMETER ON PCB WITH R,C AND PINS





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ANALOG OUTPUT TYPE ACCELEROMETERS

Measured Output No Damping

We can describe the envelope of the oscillations with the following eqn. $V_{out} = V_{max} e^{-\alpha t}$ where α is the damping coefficient



ADXL78





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OUTPUT OF PULSE WIDTH TYPE ACCELEROMETER



TEST RESULTS FOR RIT ACCELEROMETER



50 G ACCELEROMETER TESTER



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SHAKER FOR TESTING SHOCK AND VIBRATION

Electro-Dynamic Shakers



Dynamic Solutions LLC Call Us Toll Free at 877-767-7077

mailto:aimmee@dynsolusa.com,steve@dynsolusa.com

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PERMANENT MAGNET SHAKERS

Small Permanent Magnet Systems	VTS 40	VTS 65	VTS 80	VTS 100	VTS 150	
LOW COST, LOW FORCE VIBRATION SYSTEMS						
Peak Sine	40 lbf	65 lbf	80 lbf	100 lbf	150 lbf	
Amplifier Cooling Fan		INCLUDED				
Vibrator Cooling Fan	N/A	INCLUDED				
Stroke (p-p)	.75"	.75"	.75"	.75"	1.0"	
Velocity	35 ips	70 ips	80 ips	100 ips	70 ips	
Max. Acceleration (bare table)	60g	100g	115g	150g	210g	
Armature Weight	.66 lbs	.66 lbs	.70 lbs	.66 lbs	.71 lbs	
Suspension Stiffness	40 lbs./in (options available for larger payloads)					
First Major Resonance	4500 Hz	4500 Hz	7000 Hz	4500 Hz	5400 Hz	
Frequency Range	2-6500 Hz 2-8500 Hz					

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RIT VIBRATIONS LAB – DR. MARCA LAM





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Bruel & Kjaer Instruments Inc. Big Table Head Type 4813 & Exciter Body Type 4801

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LOW MASS ELECTRO-DYNAMIC SHAKER



f = 20 Hz Signal Generator = 2 Vpp Gain = 40

D = 8/32" A = $(2\pi f)^2 D$ A = 10.23 g



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p= 516

5.00kSa/

20.00ms/

LOW MASS ELECTRODYNAMIC SHAKER

Low Mass Electrodynamic Shaker

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- 3. Analog Devices Inc., Accelerometers, <u>www.Analog.com</u>

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HOMEWORK – ACCELEROMETER LAB

- 1. Determine the damping coefficient for the test fixture with no eddy current damping and with eddy current damping.
- 2. If the test fixture has an initial displacement of 3 cm, what is the maximum acceleration generated?
- 3. How can the test fixture cantilever beam resonant frequency be changed?
- 4. Under what conditions will the electrodynamic shaker generate 50 g's of acceleration?
- 5. What are the advantages of the pulse width output type of accelerometer compared to the analog output type of accelerometer?
- 6. Look up the price for some of Analog Devices accelerometers.
- 7. Describe the difference between the ADI Analog, digital, and PWM output accelerometers.

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HWACCEROMETER LAB: DAMPING

Measured Output No Damping

We can describe the envelope of the oscillations with the following eqn. $V_{out}=V_{max} e^{-\alpha t}$ where α is the damping coefficient



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LABLES FOR TEST FIXTURE



Accelerometer





Solenoid Velocity Sensor

Strain Gauge Position Sensor

Signal Conditioning

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